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(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

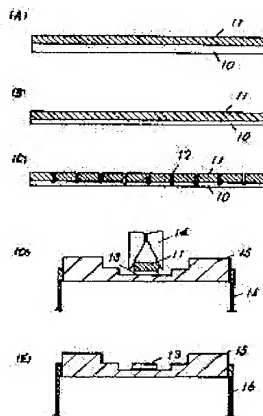
(57)Abstract:

PURPOSE: To prevent the damage generating on a semiconductor element when polishing and dicing works are performed by a method wherein reinforcement resin is applied to the surface of a semiconductor substrate.

CONSTITUTION: Reinforcement resin 11 is applied to the surface of the substrate 10 where the manufacturing process of a semiconductor element has been finished.

The thickness of said reinforcement resin 11 is to be same as that which will be polished in the following process, or a little thicker than the above. Then, the back side of a substrate 10 is polished in the thickness of the resin 11 or less than thickness. At this time, the semiconductor element formed on the surface of the semiconductor substrate 10 is protected by the

reinforcement resin 11. Subsequently, the substrate 10 is divided into pellets 13 using a dicing saw. At this time, the contamination due to water, dust and the like generated when the dicing work is performed is prevented by the reinforcement resin 11. The divided pellets 13 are die-bonded on housing case using a collet 14. The reinforcement resin 11 is removed by the heat generated when said die-bonding is performed.



LEGAL STATUS

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